Amendments to the Specification:

Please replace the third paragraph on page 1, lines 10-20, with the following replacement paragraph:

Among various semiconductor devices, there is a field effect transistor that will be mainly considered as a metal-insulator-semiconductor (MIS) transistor or a metal-oxide-semiconductor (MOS) in the instant specification and that has a source region, a drain region, and a channel region along a semiconductor surface. In this connection, the following description will be mainly made about the MOS transistor, which ~~includes the~~ is a representative MIS transistor. As well known in the art, such an MOS transistor is classified into an n-type field effect transistor (will be simply called an n-type transistor) and a p-type field effect transistor (will be simply called a p-type transistor).

Please replace the first full paragraph on page 4, lines 3-11, with the following replacement paragraph:

In order to enhance the mobility of the p-type transistor, a proposal has been made about using a (110) silicon substance which has a (110) surface with a (110) crystal plane orientation. Practically, it has been reported that using the (110) silicon substance makes it possible to raise up the mobility of the p-type transistor to about 2.5 times in comparison with the case where the (100) silicon substance is used. However, it has been pointed out also that using the (110) silicon substance brings about reducing the mobility of the n-type transistor ~~to~~ by a factor of about 0.6 ~~time~~ in comparison with the case where the (100) silicon substance is used.

Please replace the second full paragraph on page 29, lines 13-21, with the following replacement paragraph:

The gate insulation film of silicon oxynitride can be formed by the use of the microwave excitation plasma apparatus illustrated in Fig. 4. Specifically, such a silicon oxynitride film can be formed in a manner to be mentioned below. At first, the vacuum

chamber 401 illustrated in Fig. 4 is evacuated and Kr gas, O_2 gas, and NH_3 gas are filled through the shower plate 402 into the vacuum chamber 401 to a pressure of 1 Torr. On the support member 404 with the heater member, the (551) silicon substance is located and is heated to a temperature of 400°C. The temperature may fall within a range between ~~200oC~~ 200°C and ~~550oC~~ 550°C.

Please replace the second full paragraph on page 41, lines 13-23, with the following replacement paragraph:

According to the report of Kazuo Sato, et al (described in "Sensors and Actuators 73 (1999)" (pages 122 to 130), it is pointed out in Fig. 2 that striae which run in a direction of <-110> appear on a surface configuration when the surface (110) with the crystal plane orientation is subjected to alkaline etching. Surface configurations similar to the plane orientation of (110) also appear on surfaces of plane orientations that are inclined by a range between 0 and ~~12o~~ 12 degrees in a direction of <110> from (110) and that may be, for example, (551) inclined by ~~8o~~ 8 degrees. Such surface configurations appear on a plane orientation remote from (110) by ~~1o~~ 1 degree in a direction <-110>. In addition, it is possible to select crystal plane orientations which show a surface roughness behavior similar to (110) illustrated in Fig. 2.

Please replace the second paragraph on page 52, lines 4-11, with the following replacement paragraph:

When the first through the fifth steps were finished with no high frequency vibration provided in the fifth step, the contact angle was measured by dripping a water drop on the silicon surface and was equal to ~~76.4o~~ 76.4 degrees. However, when the first through the fifth steps were finished with the high frequency vibration provided in the fifth step, the contact angle was equal to ~~85.0o~~ 85.0 degrees. The results show that the high frequency vibration is effective to remove the impurity from the silicon surface and to terminate the silicon surface by hydrogen or deuterium.